

Appl. No. 09/977,069  
Amdt. dated May 23, 2003  
Reply to Office Action of February 25, 2003

PATENT

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Sub C  
B3  
Claims 1-5. (CANCELED)

Claim 6. (CURRENTLY AMENDED) A semiconductor device comprising:

- (a) a substrate;
- (b) a diffusion barrier, wherein the diffusion barrier comprises a self-assembled monolayer including a plurality of molecules, each molecule having an aromatic group at the terminus of the molecule; and
- (c) a metal layer comprising copper on the diffusion barrier, wherein for each molecule in the plurality of molecules, the copper in the metal layer is in direct contact with the aromatic group of the molecule.

7. (CURRENTLY AMENDED) The semiconductor device of claim 6 wherein the substrate comprises silicon oxide on silicon ~~and the metal layer comprises copper.~~

8. (ORIGINAL) The semiconductor device of claim 6 wherein each molecule comprises a linear carbon chain having at least 2 carbon atoms.

9. (CURRENTLY AMENDED) The semiconductor device of claim 6 wherein the metal layer is a formed by a vapor deposition process.

10. (CURRENTLY AMENDED) The semiconductor device of claim 6 wherein the diffusion barrier is capable of preventing the diffusion of ~~metal~~ copper atoms from the metal layer into the substrate when the semiconductor device is exposed to thermal annealing at 200 °C or an electric field of 2 MV/cm at 200 °C in flowing N<sub>2</sub>.

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11. (ORIGINAL) The semiconductor device of claim 6 wherein the diffusion barrier coats the walls of a hole in the substrate and wherein the metal layer fills the hole.

12. (CANCELED)

13. (CURRENTLY AMENDED) A semiconductor device comprising:

(a) a semiconductor substrate;

(b) a diffusion barrier, wherein the diffusion barrier comprises a self-assembled monolayer including a plurality of molecules, each molecule having a linear chain at least two atoms long, and an aromatic group at the terminus of the molecule; and

(c) a metal layer comprising copper on the diffusion barrier, wherein the metal layer is formed by a vapor deposition process, and wherein the copper in the metal layer is in direct contact with the aromatic group of each molecule in the self-assembled monolayer.

14. (CURRENTLY AMENDED) The semiconductor device of claim 13 wherein the substrate comprises silicon oxide on silicon ~~and the metal layer comprises copper.~~

15. (ORIGINAL) The semiconductor device of claim 13 wherein each molecule comprises a linear carbon chain having at least 2 carbon atoms.

16. (ORIGINAL) The semiconductor device of claim 13 wherein the metal layer is formed by a sputtering process.

17. (CURRENTLY AMENDED) The semiconductor device of claim 13 wherein the diffusion barrier is capable of preventing the diffusion of ~~metal~~ copper atoms from the metal layer into the substrate when the semiconductor device is exposed to thermal annealing at 200 °C or an electric field of 2 MV/cm at 200 °C in flowing N<sub>2</sub>.

18. (ORIGINAL) The semiconductor device of claim 13 wherein the substrate comprises silicon oxide on silicon.

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B<sup>3</sup> 19. (ORIGINAL) The semiconductor device of claim 13 wherein the device does not exhibit  $j_{leakage} > 1000 \text{ nAcm}^{-2}$  when the semiconductor device is exposed to thermal annealing at 200 °C or an electric field of 2 MV/cm in flowing N<sub>2</sub> at 200 °C for up to 650 minutes.

20. (CANCELED)

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